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This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

1. (Presently Amended) A method for fabricating metal wirings, comprising the steps of:

forming a ground resin film by applying a resin onto an insulating substrate;
patterning the ground resin film; and

forming a low-resistance metal film ~~selectively on and over~~ the patterned ground resin film by a wet film formation technique such that the low-resistance metal film encloses the patterned ground resin film, wherein the low-resistance metal film is a single layer film containing any one of Cu, Ni, Sn, Au, Ag, Cr, or Pd or the low-resistance metal film is a multilayer film containing at least one single layer film containing Cu, Ni, or Au.

2. (Original) A method according to Claim 1, wherein the ground resin film is made of a photosensitive resin that can be patterned by exposure and development.

3. Cancelled.

4. (Original) A method according to Claim 1, wherein the ground resin film is made of polyimide.

5. (Original) A method according to Claim 1, wherein plating is used as the wet film formation technique, and the ground resin contains a plating catalyst.

6. (Original) A method according to Claim 1, further comprising:

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a step for, before the step of forming the low-resistance metal film, modifying a surface of the ground resin film.

7. (Original) A method according to Claim 6, further comprising:
a set for, after the step of modifying the surface of the patterned ground resin film, forming on the surface-modified ground resin film a metal layer serving as a catalyst in the process of forming the low-resistance metal film by the wet film formation technique.

8. (Original) A method according to Claim 7, wherein the step of forming the metal layer acting as a catalyst in the process of forming the low-resistance metal film by the wet film formation technique comprises the steps of:
making metal ions adsorbed onto the surface-modified ground resin film; and
reducing the metal ions.

B1 9. (Original) A method according to Claim 6, wherein the ground resin film is made of a photosensitive resin which can be patterned by exposure and development.

10. Cancelled.

11. (Original) A method according to Claim 6, wherein the ground resin film is made of polyimide.

12. (Original) The metal wiring fabricating method according to claim 11, wherein the step of modifying the surface of the patterned ground resin film is a process using KOH.

13. (Original) A method according to Claim 8, wherein
the metal ions to be adsorbed onto the surface-modified ground resin are any one of Cu, Ag and Pd ions.

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14. (Original) A method according to Claim 8, wherein
the step of reducing the metal ions is a process in which ultraviolet rays are irradiated to
places where the low-resistance metal film is to be formed, by which the metal ions are
selectively reduced.

15. (Previously added) The method according to claim 1, wherein the ground resin
film has a thickness of between $0.05\ \mu\text{m}$ and $0.5\ \mu\text{m}$.
